

## Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+PNP)

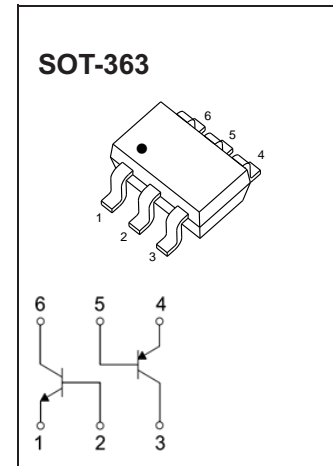
### FEATURES

- Epitaxial Planar Die Construction
- Ideal for low Power Amplification and Switching
- One 5551(NPN), one 5401(PNP)

MRKING:KNM

MAXIMUM RATINGS NPN 5551 ( $T_a=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector- Base Voltage	180	V
$V_{CEO}$	Collector-Emitter Voltage	160	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current -Continuous	0.2	A
$P_C$	Collector Power Dissipation	0.2	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	625	$^{\circ}\text{C}/\text{W}$
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS NPN 5551 ( $T_a=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=120\text{V}, I_E=0$			0.05	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4\text{V}, I_C=0$			0.05	$\mu\text{A}$
DC current gain	$h_{FE1}$	$V_{CE}=5\text{V}, I_C=1\text{mA}$	80			
	$h_{FE2}$	$V_{CE}=5\text{V}, I_C=10\text{mA}$	100		300	
	$h_{FE3}$	$V_{CE}=5\text{V}, I_C=50\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.15	V
		$I_C=50\text{mA}, I_B=5\text{mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			1	V
		$I_C=50\text{mA}, I_B=5\text{mA}$			1	V
Output Capacitance	$C_{obo}$	$V_{CB}=10\text{V}, f=1.0\text{MHz}, I_E=0$			6.0	pF
Current Gain-Bandwidth Product	$f_T$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100		300	MHz
Noise Figure	NF	$V_{CE}=5.0\text{V}, I_C=200\mu\text{A}, R_S=1.0\text{k}\Omega, f=1.0\text{kHz}$			8.0	dB

### MAXIMUM RATINGS PNP 5401 (T<sub>a</sub>=25°C unless otherwise noted)

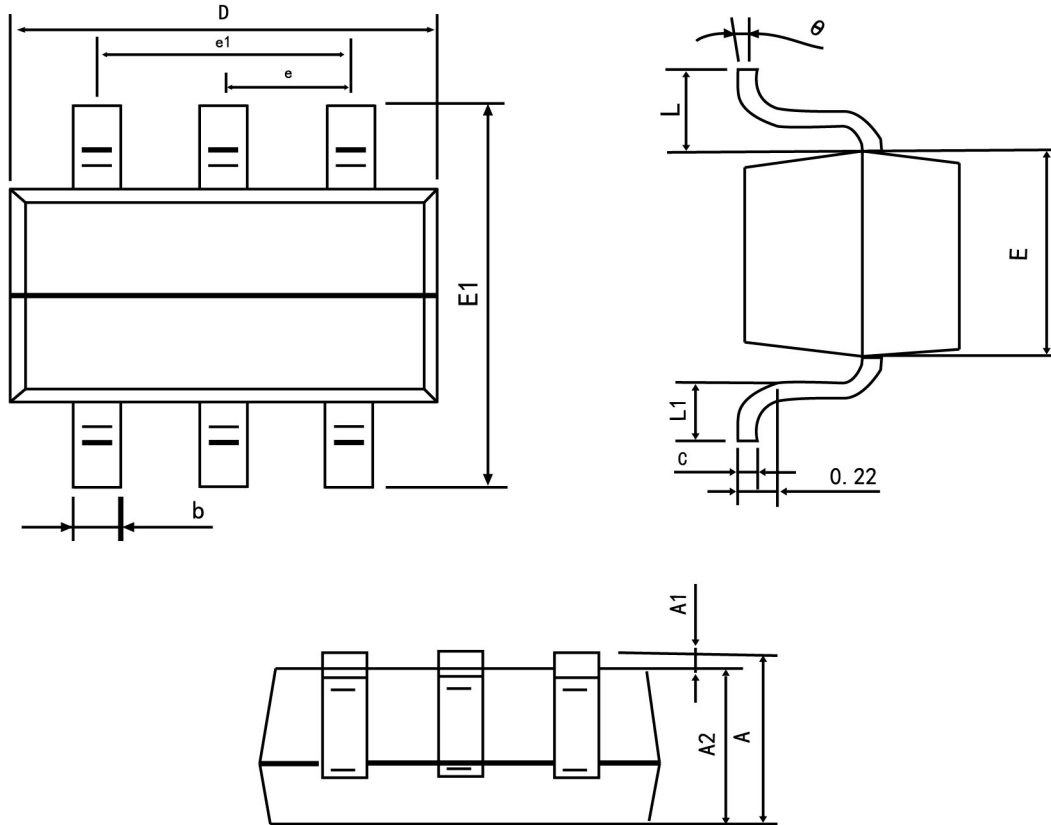
Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector- Base Voltage	-160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-150	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-0.2	A
P <sub>C</sub>	Collector Power Dissipation	0.2	W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	625	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

### ELECTRICAL CHARACTERISTICS PNP 5401 (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-160			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-150			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10μA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-120V, I <sub>E</sub> =0			-50	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-3V, I <sub>C</sub> =0			-50	nA
DC current gain	h <sub>FE1</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA	50			
	h <sub>FE2</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA	100		300	
	h <sub>FE3</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-50mA	50			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA			-0.2	V
		I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA			-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA			-1	V
		I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA			-1	V
Output Capacitance	C <sub>obo</sub>	V <sub>CB</sub> =-10V, f = 1.0MHz, I <sub>E</sub> = 0			6.0	pF
Current Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-10mA, f = 100MHz	100		300	MHz
Noise Figure	NF	V <sub>CE</sub> =-5.0V, I <sub>C</sub> =-200μA, R <sub>S</sub> = 10 Ω, f = 1.0kHz			8.0	dB



## SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°

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